

Am55/75325

Memory Drivers

Distinctive Characteristics

600mA output source/sink capability
Output short circuit protection
Two source outputs and two sink outputs

- Source strobe input and sink strobe input
- 24 volt output range
- 100% reliability assurance testing in compliance with MIL-STD-883

FUNCTIONAL DESCRIPTION

The Am55/75325 is a high-speed driver for use in magnetic memory systems. The device contains two 600mA NPN source transistor switch pairs and two 600mA NPN sink transistor switch pairs.

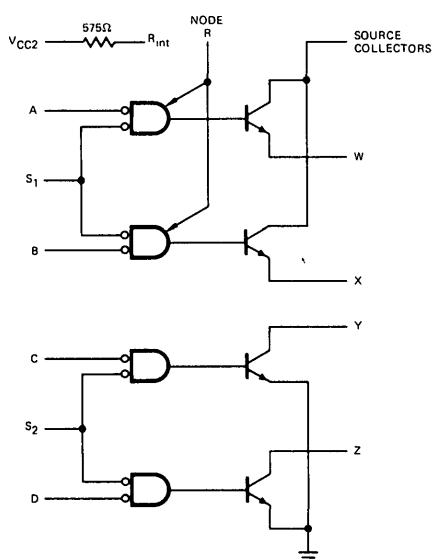
The W source output is enabled when the A input is LOW. The X source output is enabled when the B input is LOW. When the S1 source strobe input goes LOW, the selected source output will turn on. The Y sink output is enabled when the C input is LOW. The Z sink output is enabled when the D input is LOW. When the S2 sink strobe input is LOW, the selected sink output will turn on. Thus, an output can be enabled and turned on with minimum skew time.

When R_{int} and node R are connected together, the base drive for the source output transistors is set by a 575Ω internal resistor. This method provides the required base drive for source currents up to 375mA with V_{CC2} at 15V or 600mA with V_{CC2} at 24V.

When source currents greater than 375mA are used, an external resistor should be connected from V_{CC2} to node R and R_{int} should be left unconnected. This allows the base drive of the source transistors to be regulated within ±5%

Each output sink transistor has an internal pull-up resistor in parallel with a clamp diode connected to V_{CC2}. This provides protection from voltage surges associated with switching inductive loads.

LOGIC DIAGRAM

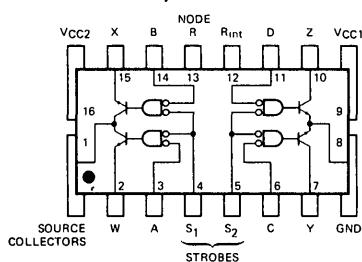


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ORDERING INFORMATION

Package Type	Temperature Range	Order Number
Molded DIP	0°C to +70°C	SN75325N
Hermetic DIP	0°C to +70°C	SN75325J
Dice	0°C to +70°C	AM75325X
Hermetic DIP	-55°C to +125°C	SN55325J
Hermetic Flat Pak	-55°C to +125°C	SN55325W
Dice	-55°C to +125°C	AM55325X

CONNECTION DIAGRAM Top View



Note: Pin 1 is marked for orientation

Am55/75325

MAXIMUM RATINGS (Above which the useful life may be impaired)

Storage Temperature	-65°C to +150°C		
Temperature (Ambient) Under Bias	-55°C to +125°C		
Supply Voltage to Ground Potential V _{CC1}	0 V to +70 V		
Supply Voltage to Ground Potential V _{CC2}	0 V to +25 V		
DC Input Voltage	-0.5 V to +5.5 V		
Continuous Total Dissipation at (or Below) 100°C Case Temperature (Note 1)	1 W		

Note 1 For operation above 100°C case temperature see derating curves

ELECTRICAL CHARACTERISTICS OVER OPERATING TEMPERATURE RANGE (Unless Otherwise Noted)

Am75325 T_A = 0°C to +70°C
Am55325 T_A = -55°C to +125°C

Parameters	Description	Test Figure	Test Conditions	Min	Typ (Note 1)	Max	Units	
V _{IH}	High Level Input Voltage	1 & 2		2.0			Volts	
V _{IL}	Low Level Input Voltage	3 & 4				0.8	Volts	
V _I	Input Clamp Voltage	5	V _{CC1} = 4.5 V V _{CC2} = 24 V I _I = -10mA T _A = 25°C		-1.3	-1.7	Volts	
I _(off)	Source Collector Terminal Off State Current	1	V _{CC1} = 4.5 V V _{CC2} = 24 V	Am55 -55°C to +125°C Am55 T _A = 25°C Am75 0°C to +70°C Am75 T _A = 25°C	500 3.0 200 3.0	150 200 200	μA	
V _{OH}	High Level Sink Output Voltage	2	V _{CC1} = 4.5 V V _{CC2} = 24 V I _O = 0	19	23		Volts	
V _(sat)	Saturation Voltage (Note 2)	3	Source Outputs	V _{CC1} = 4.5 V V _{CC2} = 15 V R _L = 24Ω I _(source) ≈ -600mA (Note 4)	Full Range (Note 3) T _A = 25°C Am55 Am75	0.9 0.43 0.43	0.7 0.75	Volts
		4	Sink Outputs	V _{CC1} = 4.5 V V _{CC2} = 15 V R _L = 24Ω I _(sink) ≈ 600mA (Note 4)	Full Range (Note 3) T _A = 25°C Am55 Am75	0.9 0.43 0.43	0.7 0.75	Volts
I _I	Input Current at Maximum Input Voltage	5	Address Inputs Strobe Inputs	V _{CC1} = 5.5 V V _{CC2} = 24 V V _{IN} = 5.5 V		1.0 2.0	mA	
I _{IH}	High Level Input Current	5	Address Inputs Strobe Inputs	V _{CC1} = 5.5 V V _{CC2} = 24 V V _{IN} = 2.4 V	3.0 6.0	40 80	μA	
I _{IL}	Low Level Input Current	5	Address Inputs Strobe Inputs	V _{CC1} = 5.5 V V _{CC2} = 24 V V _{IN} = 0.4 V	-1.0 -2.0	-1.6 -3.2	mA	
I _{CC(off)}	Supply Current All Sources and Sinks Off	6	From V _{CC1} From V _{CC2}	V _{CC1} = 5.5 V V _{CC2} = 24 V T _A = 25°C		14 7.5	22 20	mA
I _{CC1}	Supply Current from V _{CC1} Either Sink On	7		V _{CC1} = 5.5 V V _{CC2} = 24 V I _(sink) = 50mA T _A = 25°C		55	70	mA
I _{CC2}	Supply Current from V _{CC2} Either Source On	8		V _{CC1} = 5.5 V V _{CC2} = 24 V I _(source) = -50mA T _A = 25°C (Note 4)		32	50	mA

Notes 1 All typical values are at T_A = 25°C

2 Not more than one output is to be on at any one time

3 Full range for Am55325 is -55°C to 125°C and for Am75325 is 0°C to 70°C

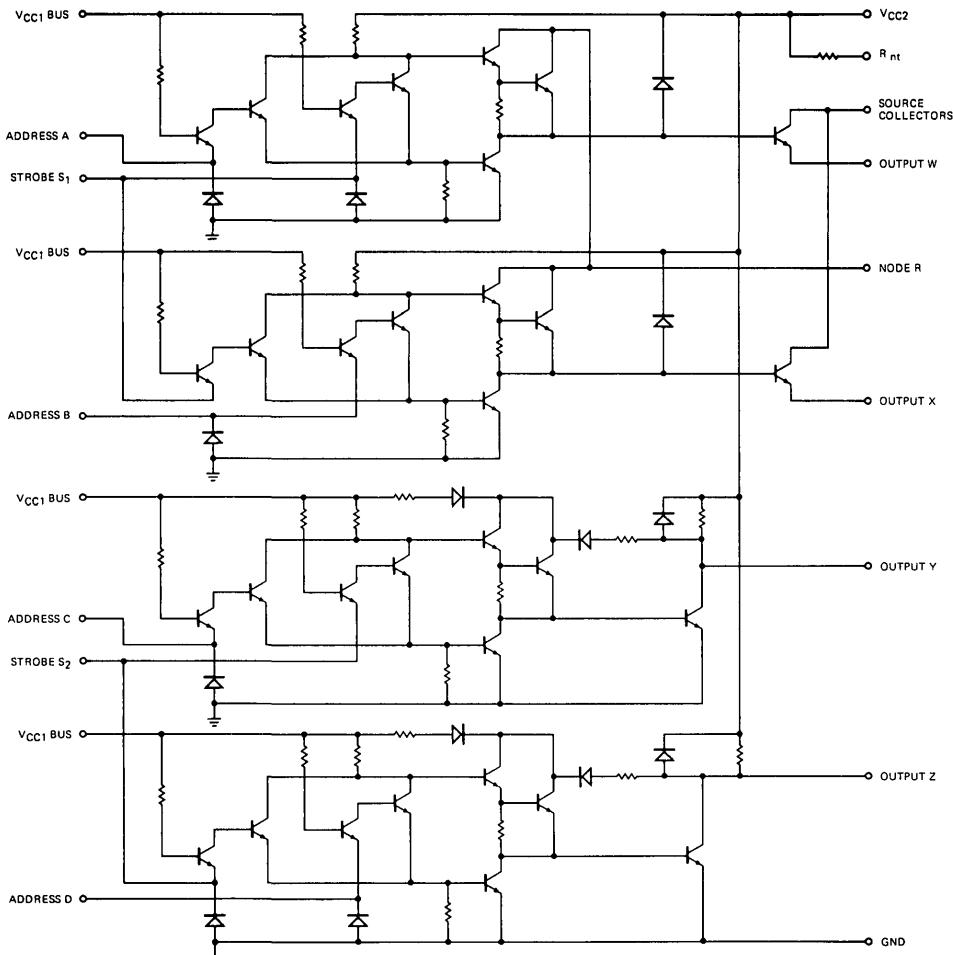
4 These parameters must be measured using pulse techniques t_w = 200μs duty cycle ≤ 2%

Switching Characteristics (V_{CC1} = 5V, T_A = 25°C)

Parameters	To (Output)	Test Figure	Test Conditions	Min	Typ	Max	Units
t _{PLH}	Source Collectors	9	V _{CC2} = 15V, R _L = 24Ω C _L = 25pF		25	50	ns
t _{PHL}					25	50	
t _{T LH}	Source Outputs	10	V _{CC2} = 20V R _L = 1kΩ C _L = 25pF		7.0		ns
t _{THL}					55		
t _{PLH}	Sink Outputs	9	V _{CC2} = 15V, R _L = 24Ω C _L = 25pF		20	45	ns
t _{PHL}					20	45	
t _{T LH}	Sink Outputs	9	V _{CC2} = 15V, R _L = 24Ω C _L = 25pF		7.0	15	ns
t _{THL}					9.0	20	
t _s	Sink Outputs	9	V _{CC2} = 15V, R _L = 24Ω C _L = 25pF		15	30	ns

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SCHEMATIC DIAGRAM



FUNCTION TABLE

ADDRESS INPUTS		STROBE INPUTS		OUTPUTS			
Source A	Sink B	Source C	Sink D	Source S1	Sink S2	Source W	Sink X
L	H	X	X	L	H	ON	OFF
H	L	X	X	L	H	OFF	ON
X	X	L	H	H	L	OFF	OFF
X	X	H	L	H	L	OFF	OFF
X	X	X	X	H	H	OFF	OFF
H	H	H	H	X	X	OFF	OFF

H = HIGH

L = LOW

X = Don't Care

Note Not more than one output is to be on at any one time

DEFINITION OF FUNCTIONAL TERMS

A The enable input for the W source output When the A input is LOW, the W output is enabled

B The enable input for the X source output When the B input is LOW, the X output is enabled

C The enable input for the Y sink output When the C input is LOW, the Y output is enabled

D The enable input for the Z sink output When the D input is LOW, the Z output is enabled

S1 The strobe input for the source drivers When the S1 input is LOW, the enabled source driver is on

S2 The strobe input for the sink drivers When the S2 input is LOW, the enabled sink driver is on

W, X The two source driver outputs

Y, Z The two sink driver outputs

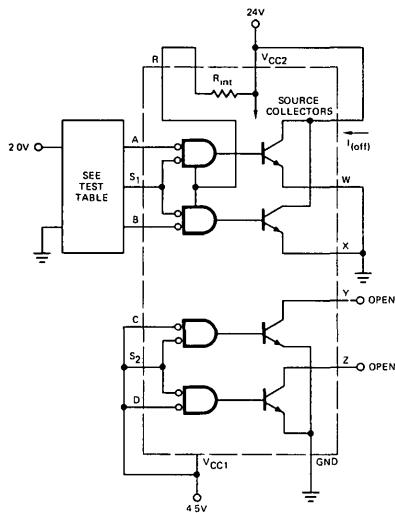
Source Collectors The common node of the driver transistors of the source outputs

R_{int} The node for a 575Ω internal resistor The other terminal of the resistor is connected internally to VCC2

R The base drive node of the output source transistor drivers

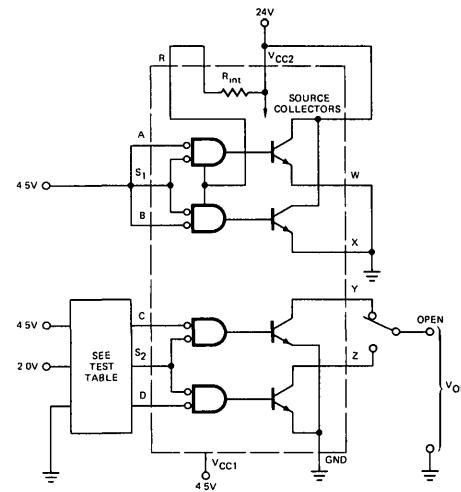
DC PARAMETER MEASUREMENT INFORMATION

DC TEST CIRCUITS



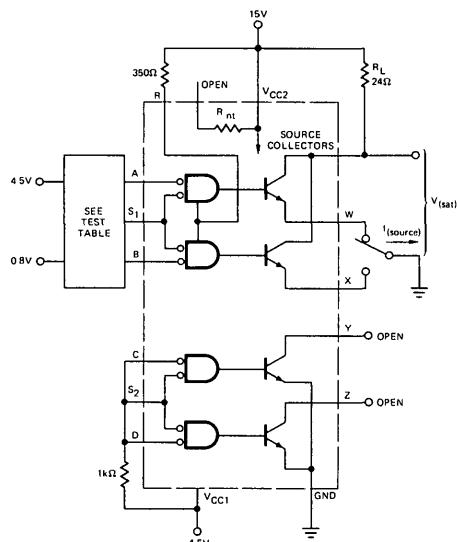
TEST TABLE

A	B	S1
GND	GND	2V
2V	2V	GND

Figure 1. V_{IH} and $I_{(off)}$ 

TEST TABLE

C	D	S2	Y	Z
2V	4.5V	GND	V_{OH}	OPEN
GND	4.5V	2V	V_{OH}	OPEN
4.5V	2V	GND	OPEN	V_{OH}
4.5V	GND	2V	OPEN	V_{OH}

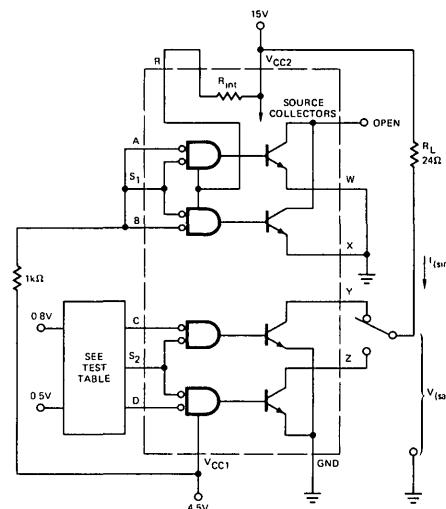
Figure 2. V_{IH} and V_{OH} 

Note

These parameters must be measured using pulse techniques
 $t_w = 200\mu s$ duty cycle $\leq 2\%$

TEST TABLE

A	B	S1	W	X
0.8V	4.5V	0.8V	GND	OPEN
4.5V	0.8V	0.8V	OPEN	GND

Figure 3. V_{IL} and Source $V_{(sat)}$ 

Note

These parameters must be measured using pulse techniques
 $t_w = 200\mu s$ duty cycle $\leq 2\%$

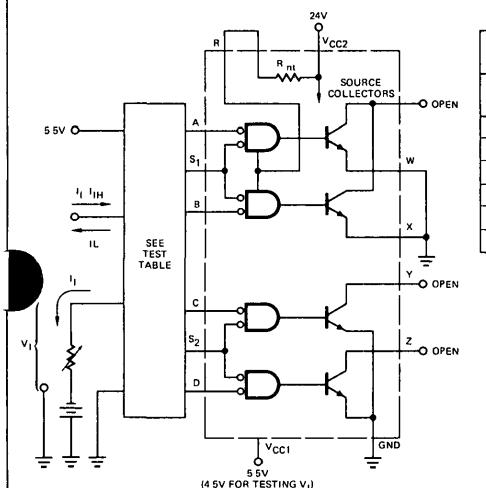
TEST TABLE

C	D	S2	Y	Z
0.8V	4.5V	0.8V	R_L	OPEN
4.5V	0.8V	0.8V	OPEN	R_L

Figure 4. V_{IL} and Sink $V_{(sat)}$

DC PARAMETER MEASUREMENT INFORMATION (Cont.)

DC TEST CIRCUITS



I _I , I _{IIH}	
Apply V _I = 55 V, Measure I _I	
Apply V _I = 24 V, Measure I _{IIH}	Ground
A	S1
S1	A B
B	S1
C	S2
S2	C D
D	S2
	A S1 B C

	V _I , I _{IL}
Apply V _I = 0 4V Measure I _{IL}	
Apply I _L = -10 mA Measure V _I	Apply 5 5V
A	S1 B C S2 D
S1	A B C S2 D
B	A S1 C S2 D
C	A S1 B S2 D
S2	A S1 B C D
D	A S1 B C S2

Figure 5 V_L , I_L , I_{IH} , and I_{IL}

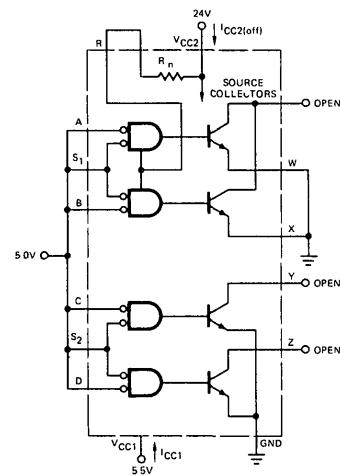
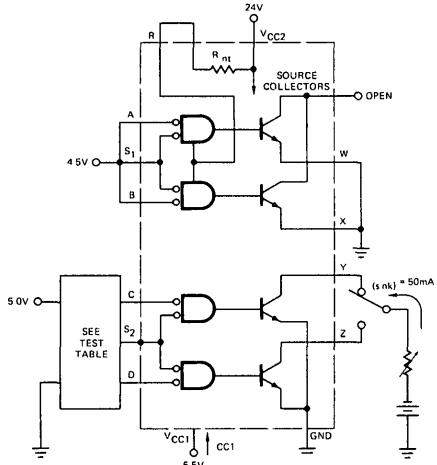


Figure 6 $I_{CC1(off)}$ and $I_{CC2(off)}$

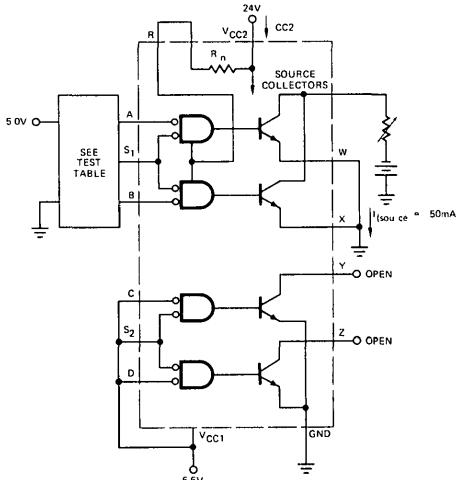
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TEST TABLE

TEST TABLE				
C	D	S2	Y	Z
GND	5V	GND	I _(sink)	OPEN
5V	GND	GND	OPEN	I _(sink)

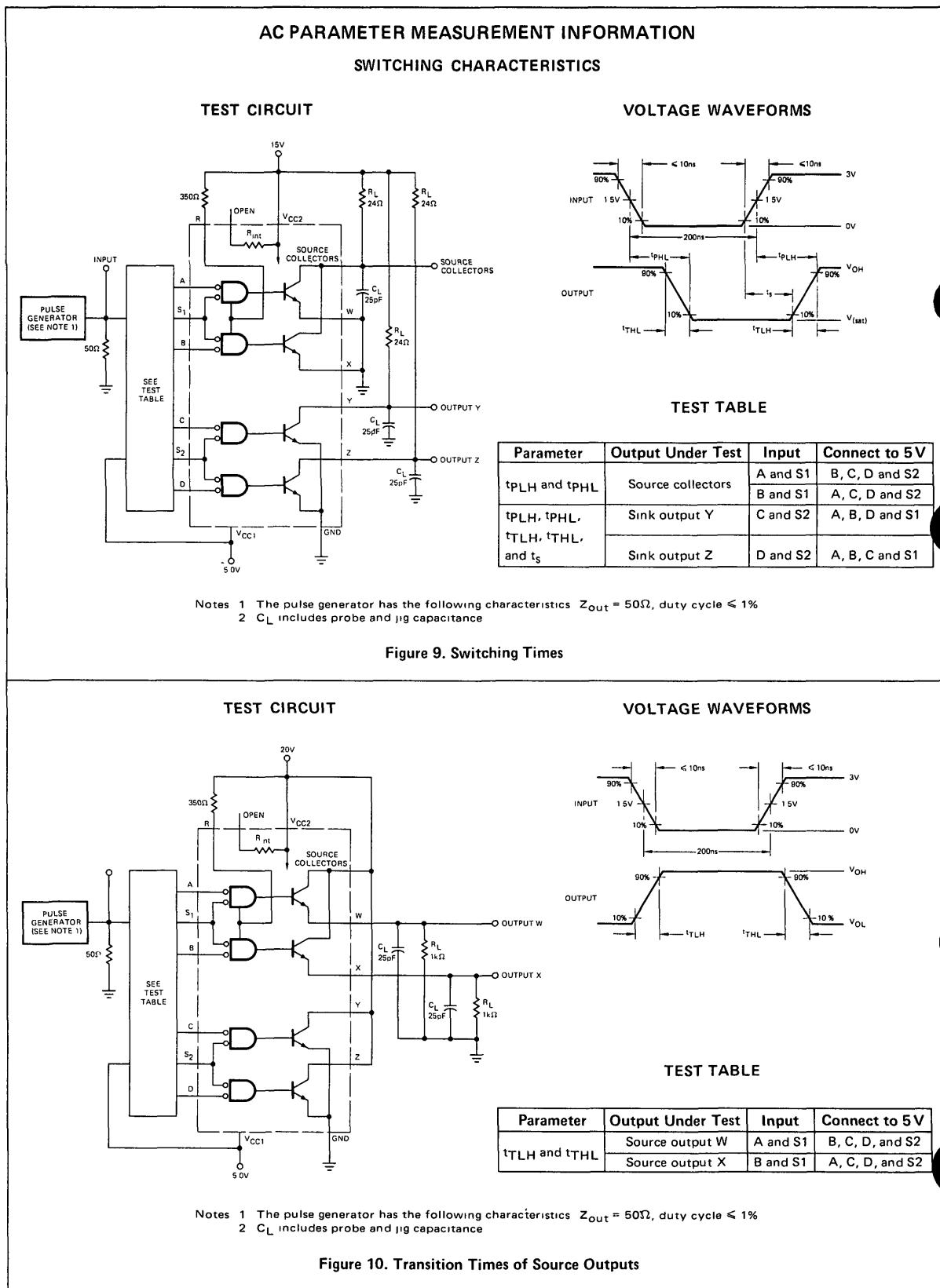
Figure 7 I_{CC1} , Either Sink On



TEST TABLE

TEST TABLE		
A	B	S1
GND	5V	GND
5V	GND	GND

Figure 8 Icc₂, Either Source On



TYPICAL CHARACTERISTICS

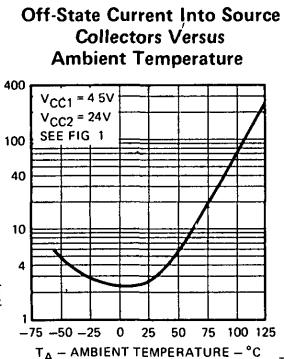


Figure 11

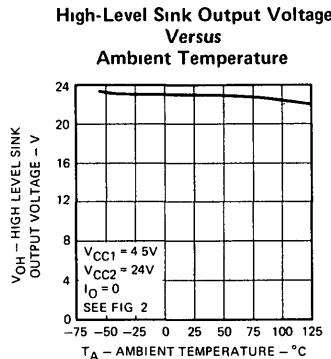


Figure 12

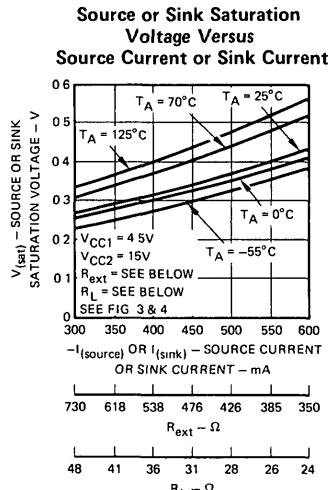


Figure 13

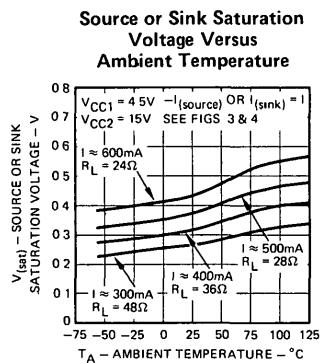


Figure 14

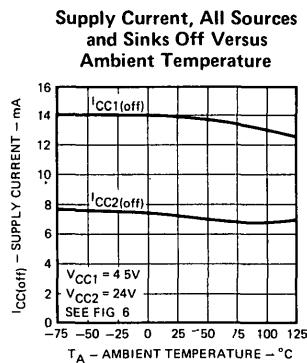
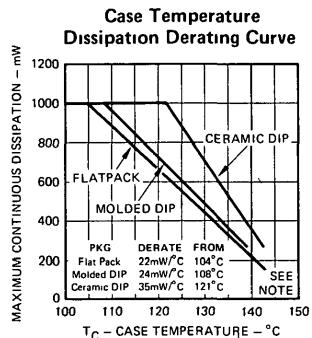


Figure 15



Note Rated operating ambient temperature ranges must be observed regardless of heat sinking

Figure 16

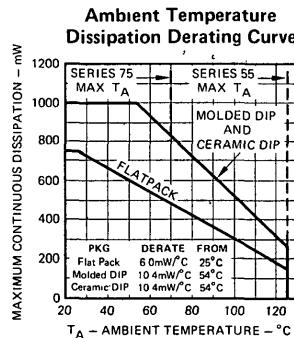


Figure 17

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APPLICATIONS

External Resistor Calculation

The value of the external pull up resistor (R_{ext}) for a particular memory application may be determined as

$$R_{ext} = \frac{16 [V_{CC2(min)} - V_S - 2.2]}{I_L - 16 [V_{CC2(min)} - V_S - 2.9]}$$

where R_{ext} is in $k\Omega$,

$V_{CC2(min)}$ is the lowest expected value of V_{CC2} in volts,
 V_S is the source output voltage in volts with respect to ground, I_L is in mA

The power dissipated in resistor R_{ext} during the load current pulse duration is calculated as

$$P_{Rext} \approx \frac{I_L}{16} [V_{CC2(min)} - V_S - 2]$$

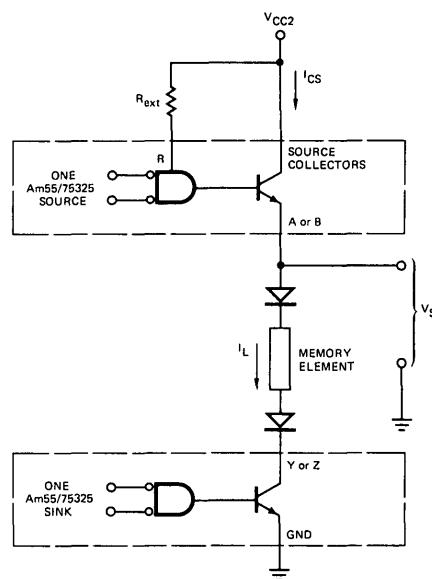
where P_{Rext} is in mW

After solving for R_{ext} , the magnitude of the source collector current (I_{CS}) is determined from

$$I_{CS} \approx 0.94 I_L$$

where I_{CS} is in mA

The regulated source output transistor base current through the external pull up resistor (R_{ext}) and the source gate and I_{CS} comprise I_L



Notes
1 For clarity partial logic diagrams of two Am75325's are shown
2 Source and sink shown are in different packages

Metallization and Pad Layout

